## **TSHG5210**



**Vishay Semiconductors** 

## High Speed Infrared Emitting Diode, 850 nm, **GaAlAs Double Hetero**



### **FEATURES**

- · Package type: leaded
- Package form: T-1¾
- Dimensions (in mm): Ø 5
- · Leads with stand-off
- Peak wavelength: λ<sub>p</sub> = 850 nm
- High reliability
- High radiant power
- · High radiant intensity
- Angle of half intensity:  $\phi = \pm 10^{\circ}$
- · Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth: f<sub>c</sub> = 18 MHz
- · Good spectral matching with CMOS cameras
- · Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### Note

Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

#### APPLICATIONS

- Infrared radiation source for operation with CMOS cameras
- High speed IR data transmission
- Smoke-automatic fire detectors

### DESCRIPTION

TSHG5210 is an infrared, 850 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

PRODUCT SUMMARY					
COMPONENT	l <sub>e</sub> (mW/sr)	φ (deg)	λ <sub>p</sub> (nm)	t <sub>r</sub> (ns)	
TSHG5210	230	± 10	850	20	

#### Note

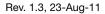
Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSHG5210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾		

Note

MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_{amb} = 25 \text{ °C}$ , unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V <sub>R</sub>	5	V	
Forward current		I <sub>F</sub>	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I <sub>FM</sub>	200	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1	A	
Power dissipation		Pv	180	mW	
Junction temperature		Тj	100	°C	
Operating temperature range		T <sub>amb</sub>	- 40 to + 85	°C	
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	230	K/W	



Document Number: 81810



GREEN

(5-2008)\*\*



For technical questions, contact: emittertechsupport@vishay.com

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

## Vishay Semiconductors



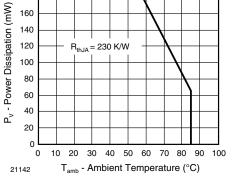


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

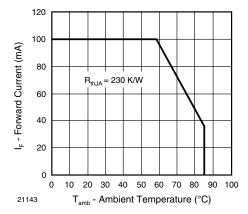


Fig. 1 - Forward Current Limit vs. Ambient Temperature

<b>BASIC CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	V <sub>F</sub>		1.5	1.8	V
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	V <sub>F</sub>		2.3		V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 mA	TK <sub>VF</sub>		- 1.8		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			10	μA
Junction capacitance	$V_{R} = 0 V, f = 1 MHz, E = 0$	Cj		125		pF
<b>D H H H</b>	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l <sub>e</sub>	140	230	420	mW/sr
Radiant intensity	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	l <sub>e</sub>		2300		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	φ <sub>e</sub>		55		mW
Temperature coefficient of $\phi_{\text{e}}$	l <sub>F</sub> = 100 mA	TKφ <sub>e</sub>		- 0.35		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	l <sub>F</sub> = 100 mA	λ <sub>p</sub>	820	850	880	nm
Spectral bandwidth	l <sub>F</sub> = 100 mA	Δλ		40		nm
Temperature coefficient of $\lambda_p$	l <sub>F</sub> = 100 mA	TKλp		0.25		nm/K
Rise time	l <sub>F</sub> = 100 mA	t <sub>r</sub>		20		ns
Fall time	l <sub>F</sub> = 100 mA	t <sub>f</sub>		13		ns
Cut-off frequency	$I_{DC} = 70$ mA, $I_{AC} = 30$ mA pp	f <sub>c</sub>		18		MHz
Virtual source diameter		d		3.7		mm

For technical questions, contact: <u>emittertechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>





**Vishay Semiconductors** 

### BASIC CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

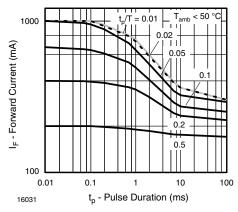


Fig. 2 - Pulse Forward Current vs. Pulse Duration

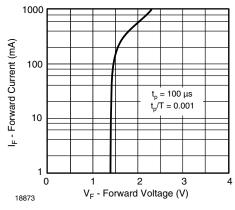


Fig. 3 - Forward Current vs. Forward Voltage

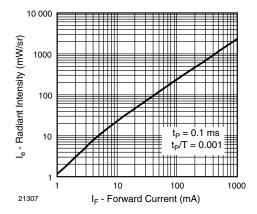


Fig. 4 - Radiant Intensity vs. Forward Current

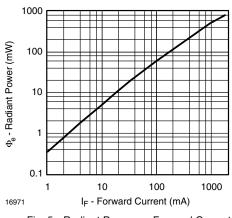


Fig. 5 - Radiant Power vs. Forward Current

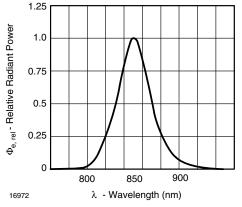


Fig. 6 - Relative Radiant Power vs. Wavelength

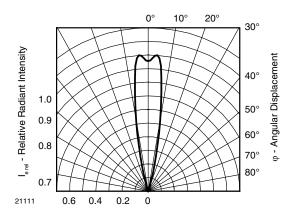


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

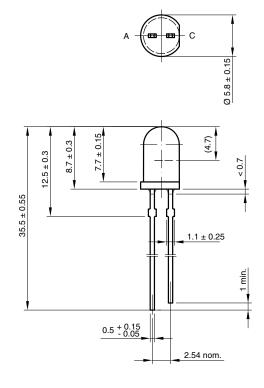
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

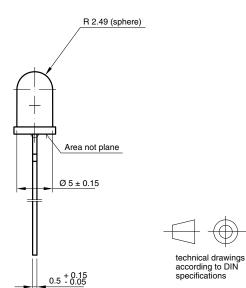


Vishay Semiconductors



### **PACKAGE DIMENSIONS** in millimeters







6.544-5258.02-4 Issue: 7; 23.07.10 95 10916

Document Number: 81810



Vishay

## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Vishay: TSHG5210